SILICON (Si) POWER MOSFET A CET0215SL



CET0215SL

150V ▲ 370mΩ ▲ 2A ▲ Si MOSFET

SILICON Si MOSFET ▲ SMD type N-channel enhancement mode UL94V-0 rated flame retardant epoxy SOT223 package ▲ MSL 3 Super high dense cell density for extremely low R_{DS(ON)} Rugged and reliable

MGT **A** Manufacturer Group of Technology





RoHS

REACH

MAXIMUM RATINGS

Parameter ($T_A = 25^{\circ}C$, unless otherwise noted)	Characteristics	
Drain-Source Voltage	V _{DS}	150V
Gate-Source Voltage	V _{GS}	±16V
Continuous Drain Current	I _D	2A
Pulsed Drain Current Note 1	I _{DM}	8A
Maximum Power Dissipation	PD	3W
Operating and Storage Temperature Range	T _J , T _{STG}	-55°C to +150°C

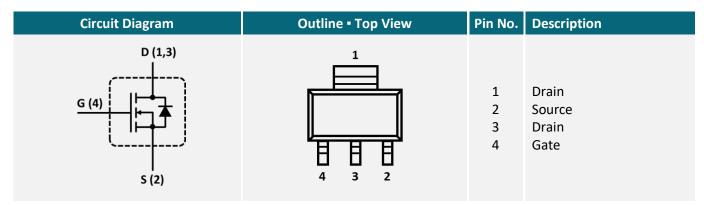
THERMAL CHARACTERISTICS

Parameter	Symbol	Limit
Thermal Resistance, Junction-to-Case Note 2	R _{TH_JC}	42°C/W

APPLICATIONS

Audio	Industrial	Power over	Power	UPS
Amplifier	Control	Ethernet	Inverter	
()		РоЕ		

PIN DESCRIPTION



CET0215SL Rev.001 Date: 30/09/2022 Page: 1

Copyright by MGT A www.mgt.co.com A All rights reserved A The information in this document is subject to change without notice.



CET MOS

ELECTRICAL CHARACTERISTICS A T_A = 25°C, unless otherwise noted

ltem	Condition	Symbol	Min.	Тур.	Max.	Unit
Off Characteristics						
Drain-Source Breakdown Voltage	$V_{GS} = 0V, I_{D} = 250\mu A$	BV _{DSS}	150			V
Zero Gate Voltage Drain Current	V_{DS} = 150V, V_{GS} = 0V	I _{DSS}			1	μΑ
Gate Body Leakage Current, Forward	$V_{GS} = 16V$, $V_{DS} = 0V$	I _{GSSF}			100	nA
Gate Body Leakage Current, Reverse	V_{GS} = -16V, V_{DS} = 0V	I _{GSSR}			-100	nA
On Characteristics Note 3						
Gate Threshold Voltage	$V_{GS} = V_{DS}, I_{D} = 250 \mu A$	$V_{GS(th)}$	0.4		1.4	V
Static Drain-Source On-Resistance	$V_{GS} = 10V, I_{D} = 1A$	R _{DS(ON)}		370	440	mΩ
Static Drain-Source On-Resistance	$V_{GS} = 5V$, $I_D = 1A$	R _{DS(ON)}		380	500	mΩ
Static Drain-Source On-Resistance	$V_{GS} = 3V$, $I_D = 1A$	R _{DS(ON)}		420	550	mΩ
Dynamic Characteristics Note 4						
Input Capacitance	$V_{DS} = 25V, V_{GS} = 0V, f = 1MHz$	C _{ISS}		380		рF
Output Capacitance	V_{DS} = 25V, V_{GS} = 0V, f = 1MHz	Coss		85		рF
Reverse Transfer Capacitance	V_{DS} = 25V, V_{GS} = 0V, f = 1MHz	C _{RSS}		30		рF
Switching Characteristics Note 4						
Turn-On Delay Time	V_{DD} = 50V, V_{GS} = 10V, I_{D} = 1A, $R_{\text{G}(\text{ext})}$ = 22 Ω	t _{D(ON)}		6		ns
Turn-On Rise Time	V_{DD} = 50V, V_{GS} = 10V, I_{D} = 1A, $R_{\text{G(ext)}}$ = 22 Ω	t _R		5		ns
Turn-Off Delay Time	V_{DD} = 50V, V_{GS} = 10V, I_{D} = 1A, $R_{\text{G(ext)}}$ = 22 Ω	t _{D(OFF)}		62		ns
Turn-Off Fall Time	V_{DD} = 50V, V_{GS} = 10V, I_{D} = 1A, $R_{G(ext)}$ = 22 Ω	t _F		11		ns
Total Gate Charge	V_{DS} = 80V, V_{GS} = 4.5V, I_{D} = 1.8A	Q_{G}		7.3		nC
Gate Source Charge	V_{DS} = 80V, V_{GS} = 4.5V, I_{D} = 1.8A	Q _{GS}		0.5		nC
Gate Drain Charge	V_{DS} = 80V, V_{GS} = 4.5V, I_{D} = 1.8A	\mathbf{Q}_{GD}		3.1		nC
Drain-Source Diode Characteristics a	nd Maximum Ratings					
Drain-Source Diode Forward Current ^{Note 3}		Is			2	А
Drain-Source Diode Forward Voltage ^{Note 3}	V _{GS} = 0V, I _S = 1.85A	V_{SD}			1.2	V

Notes

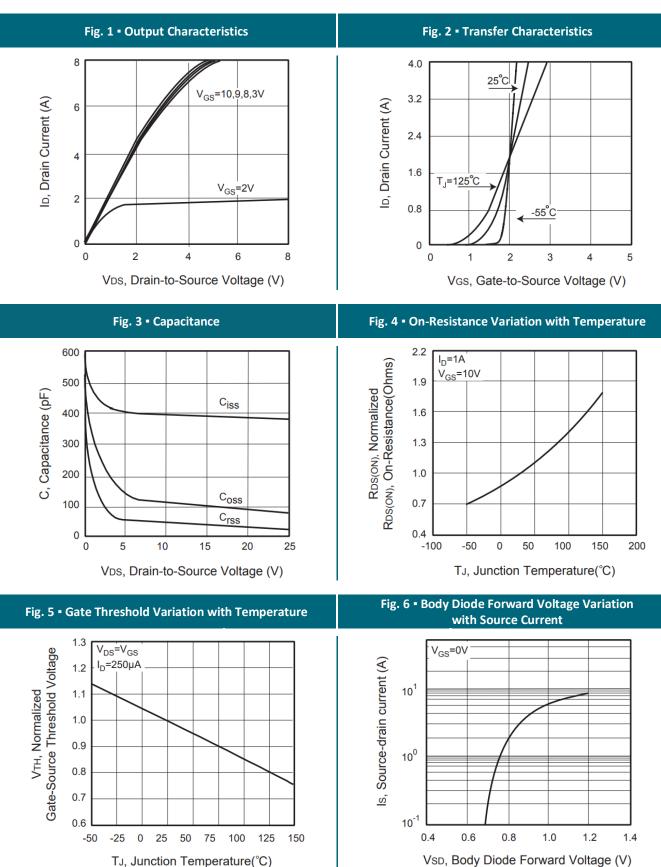
- 1: Repetitive Rating: Pulse width limited by maximum junction temperature
- 2: Surface Mounted on FR4 Board, $t \le 10$ sec
- 3: Pulse Test: Pulse Width \leq 300µs, Duty Cycle \leq 2%.
- 4: Guaranteed by design, not subject to production testing.



MGT **A** Manufacturer Group of Technology

CET MOS

REFERENCE DATA ▲ TYPICAL DEVICE PERFORMANCE



Copyright by MGT A www.mgt.co.com A All rights reserved A The information in this document is subject to change without notice.



10m 100ms

10²

toff -

10%

90%

MGT 🔺 Manufacturer Group of Technology

50%

50%

PULSE WIDTH

Vin

10%

90%

tf

10

10³

CET MOS

REFERENCE DATA A TYPICAL DEVICE PERFORMANCE

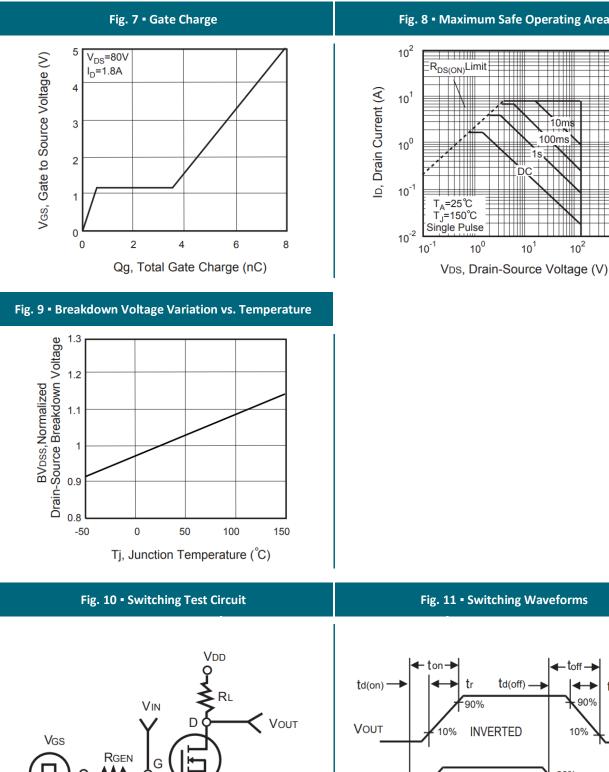


Fig. 8 • Maximum Safe Operating Area

CET0215SL ▲ Rev.001 ▲ Date: 30/09/2022 ▲ Page: 4

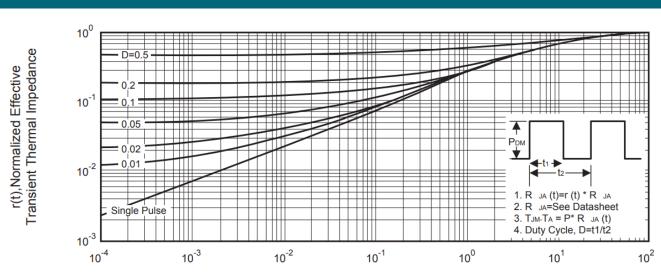
S

Copyright by MGT A www.mgt.co.com A All rights reserved A The information in this document is subject to change without notice.



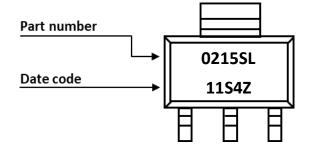
CET MOS

REFERENCE DATA ▲ TYPICAL DEVICE PERFORMANCE



Square Wave Pulse Duration (sec)

PART MARKING



DATE CODE

Example: 11S4Z



U	1	2	3	4
2020	2021	2022	2023	2024
5	6	7	8	9
	6 2026			
				U 1 2 3 2020 2021 2022 2023

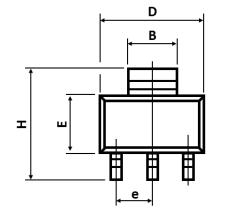
MGT **A** Manufacturer Group of Technology

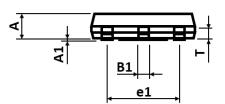
Fig. 12 • Normalized Thermal Transient Impedance Curve

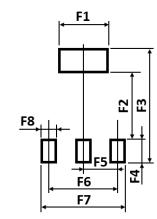


CET MOS

PACKAGE OUTLINE AND RECOMMENDED PAD LAYOUT







Sym	Millimeters (Min.)		
А	1.500	-	1.700
A1	0.020	-	0.100
В	2.950	-	3.200
B1	0.670	-	0.800
С	0.240	-	0.350
D	6.300	-	6.850
е		2.300 TYP	

Sym	Millimeters (Min.)	Millimeters (Typ.)	Millimeters (Max.)				
e1		4.600 TYP					
E	3.300	-	3.800				
н	6.700	-	7.300				
L	0.900	-	-				
Т	0.600	-	0.800				
θ	10° MAX						

Sym	Millimeters (Min.)	Millimeters (Typ.)	Millimeters (Max.)	Sym	Millimeters (Min.)	Millimeters (Typ.)	Millimeters (Max.)
F1	-	3.500	-	F5	-	2.300	-
F2	-	4.600	-	F6	-	4.600	-
F3	-	8.000		F7	-	5.600	-
F4	-	1.600		F8	-	1.200	-

θ

Notes: 1. The suggested land pattern dimensions have been provided for reference only.

2. For further information, please reference document IPC-7351A.

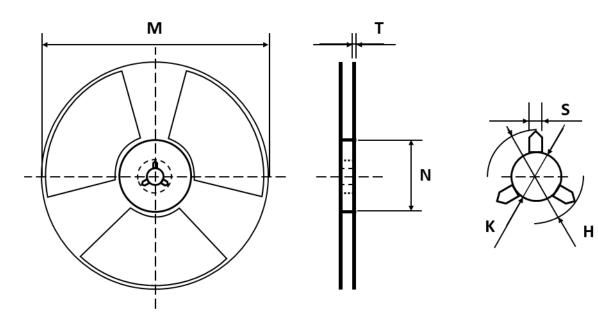
ORDERING INFORMATION

Part Number	Package	Packing	Reel Qty.	Inner Box Qty.	Outer Box Qty.
CET0215SL	SOT223	7" Reel	2,500pcs	5,000pcs	15,000pcs



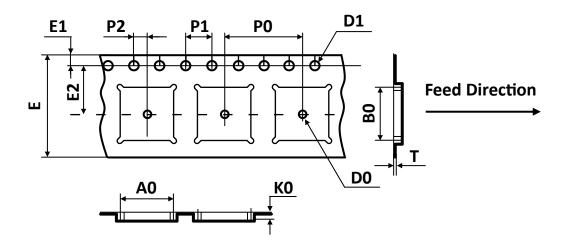


REEL DIMENSIONS All dimensions in mm



Tape Size	Reel Size	М	Ν	т	Н	К	S
8mm	Ø180	Ø178.00	Ø54.00	1.20	20.00	13.30	3.00
011111	Ø190	±1.00	±0.50	±0.20	±1.00	±0.30	±1.00

TAPE DIMENSIONS All dimensions in mm



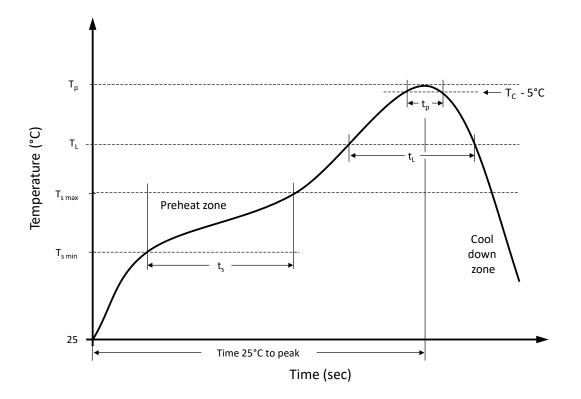
Packag	e A0	B0	К0	D0	D1	E	E1	E2	P0	P1	P2	Т
SOT22	2.40	2.60	1.20	1.00	1.50	8.00	1.75	3.50	4.00	4.00	2.00	0.20
30122	±0.10	±0.10	±0.10	±0.10	±0.10	±0.10	±0.10	±0.10	±0.10	±0.10	±0.05	±0.02

Note: All dimensions meet EIA-481-D requirements.





RECOMMENDED REFLOW SOLDERING PROFILE



Recommended reflow soldering conditions ▲ **Refer to JEDEC J-STD-020E**

Profile Features		Sn-Pb Eutetic Assembly	Pb-Free Assembly
Preheat temperature min.	T_{smin}	100 °C	150 °C
Preheat temperature max.	$T_{s max}$	150 °C	200 °C
Preheat time t_s from $T_{s min}$ to $T_{s max}$	ts	120 seconds	120 seconds
Ramp-up rate (T _L to T _p)		max. 3 °C/second	max. 3 °C/second
Liquidous temperature	ΤL	183 °C	217 °C
Time t_L maintained above T_L	t∟	150 seconds max.	150 seconds max.
Peak package body temperature	Tp	235°C	260°C
Timeframe of within 5°C below and up to max actual peak body temperature	tp	20 seconds max.	30 seconds max.
Ramp-down rate (T_L to T_p)		max. 6 °C/second	max. 6 °C/second
Time 25°C to peak temperature		max. 6 minutes	max. 8 minutes

MGT **A** Manufacturer Group of Technology

Copyright by MGT \blacktriangle www.mgt.co.com \blacktriangle All rights reserved \blacktriangle The information in this document is subject to change without notice.



REVISION TABLE

Revision	Date	Status	Notes
001	30/09/2022	Initial release	Initial publication

DISCLAIMER

Except for the written expressed warranties, MGT does not implicitly, by assumption or whatever else, warrant, under-take, promise any other warranty or guaranty for any MGT product.

All information and technical specifications made available by MGT are for guidance only and we reserve the right to change or modify them without prior notice. Unless expressly stated in writing by MGT, we reject any guarantees, obligations, or warranties.

All MGT products with the technical specifications described are suitable for use in certain applications. Operating, production, storage and environmental conditions can have a massive influence on the parameters mentioned in the data sheets, which cause the performance to vary over time.

It is subject to the user's duty of care to design and validate his products in such a way that appropriate measures are taken, such as protective circuits or redundant systems to ensure the safety standards required in the application.

MGT components are not designed or rated for use in life support, rescue, safety critical, military, or aerospace applications where failure or malfunction could result in property or environmental damage, serious injury or death. In the aforementioned cases, please contact us before using MGT products.

In principle, we reserve all rights and MGT's general terms and conditions apply. You can find them on our website <u>www.mgt.co.com.</u>